

MOS FIELD EFFECT POWER TRANSISTOR

2SK1499/2SK1500

SWITCHING

N-CHANNEL POWER MOS FET

INDUSTRIAL USE

DESCRIPTION

The 2SK1499/2SK1500 is N-channel MOS Field Effect Transistor designed for high voltage switching applications.

FEATURES

- Low On-state Resistance
 $R_{DS(on)} \leq 0.25 \Omega / 0.27 \Omega$ ($V_{GS} = 10 \text{ V}$, $I_D = 13 \text{ A}$)
- Low C_{iss} $C_{iss} = 3\ 300 \text{ pF TYP.}$
- Built-in G-S Gate Protection Diode
- High Avalanche Capability Ratings

QUALITY GRADE

Standard

Please refer to "Quality grade on NEC Semiconductor Devices" (Document number IEI-1209) published by NEC Corporation to know the specification of quality grade on the devices and its recommended applications.

ABSOLUTE MAXIMUM RATINGS ($T_a = 25^\circ\text{C}$)

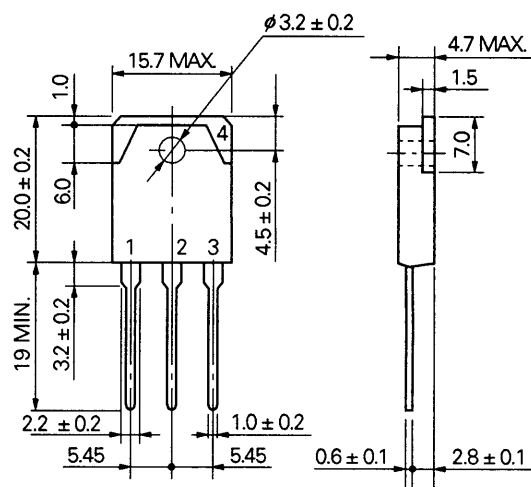
Drain to Source Voltage	V_{DSS}	450/500	V
(2SK1499/2SK1500)			
Gate to Source Voltage	V_{GSS}	± 30	V
Drain Current (DC)	$I_{D(DC)}$	± 25	A
Drain Current (pulse)	$I_{D(pulse)}^*$	± 100	A
Total Power Dissipation ($T_c = 25^\circ\text{C}$)	P_T	160	W
Channel Temperature	T_{ch}	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55 to $+150$	$^\circ\text{C}$
Single Avalanche Current	I_{AS}^{**}	37.5	A
Single Avalanche Energy	E_{AS}^{**}	907	mJ

* $PW \leq 10 \mu\text{s}$, Duty Cycle $\leq 2\%$

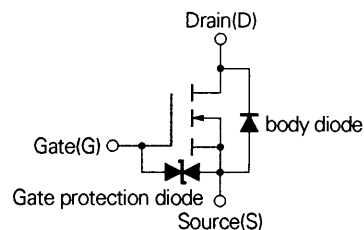
** Starting $T_{ch} = 25^\circ\text{C}$, $R_G = 25 \Omega$, $V_{GS} = 20 \text{ V} \rightarrow 0$

PACKAGE DIMENSIONS

(in millimeters)



1. Gate
2. Drain
3. Source
4. Fin (Drain)

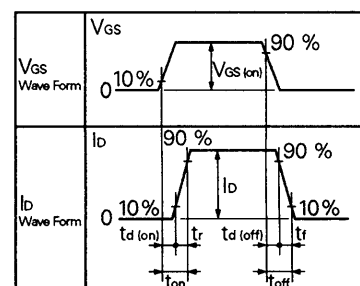
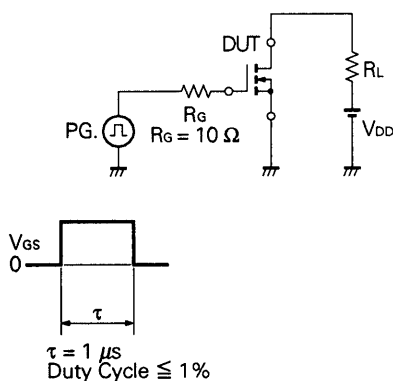
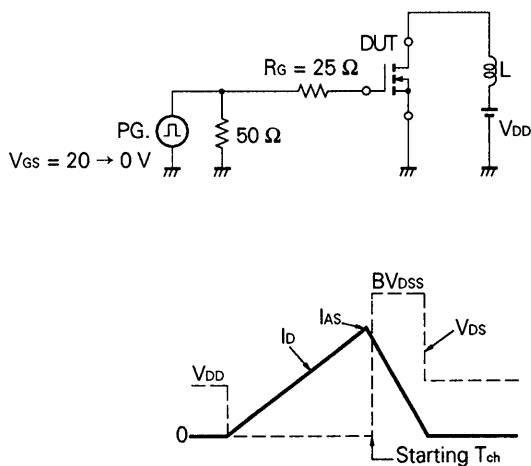


ELECTRICAL CHARACTERISTICS (T_a = 25 °C)

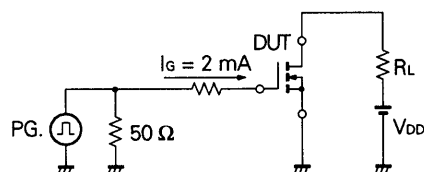
CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITIONS
Drain to Source On-state Resistance (2SK1499)	R _{DS(on)}		0.20	0.25	Ω	V _{GS} = 10 V, I _D = 13 A
Drain to Source On-state Resistance (2SK1500)	R _{DS(on)}		0.22	0.27	Ω	
Gate to Source Cutoff Voltage	V _{GS(off)}	2.5		3.5	V	V _{DS} = 10 V, I _D = 1 mA
Forward Transfer Admittance	y _{fs}	8.0			S	V _{DS} = 10 V, I _D = 13 A
Drain Leakage Current (2SK1499)	I _{DSS}			100	μA	V _{DS} = 450 V, V _{GS} = 0
Drain Leakage Current (2SK1500)	I _{DSS}			100	μA	V _{DS} = 500 V, V _{GS} = 0
Gate to Source Leakage Current	I _{GSS}			±10	μA	V _{GS} = ±30 V, V _{DS} = 0
Input Capacitance	C _{iss}		3 300		pF	V _{DS} = 10 V V _{GS} = 0 f = 1 MHz
Output Capacitance	C _{oss}		1 100		pF	
Reverse Transfer Capacitance	C _{rss}		480		pF	
Turn-On Delay Time	t _{d(on)}		50		ns	V _{GS} = 10 V V _{DD} = 150 V I _D = 13 A, R _G = 10 Ω R _L = 11.5 Ω
Rise Time	t _r		130		ns	
Turn-Off Delay Time	t _{d(off)}		180		ns	
Fall Time	t _f		70		ns	
Total Gate Charge	Q _G		115		nC	V _{GS} = 10 V I _D = 25 A V _{DD} = 400 V
Gate to Source Charge	Q _{GS}		20		nC	
Gate to Drain Charge	Q _{GD}		70		nC	
Diode Forward Voltage	V _{F(S-D)}		1.0		V	I _D = 25 A, V _{GS} = 0
Reverse Recovery Time	t _{rr}		670		ns	I _D = 25 A, V _{GS} = 0 di/dt = 50 A/μs
Reverse Recovery Charge	Q _{rr}		7.0		μC	

Test Circuit 1: Avalanche Capability

Test Circuit 2: Switching Time

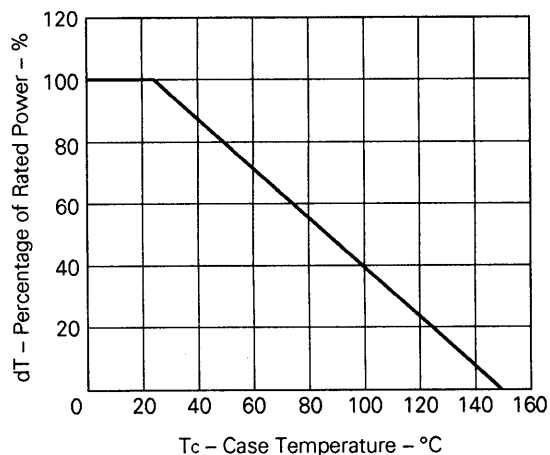


Test Circuit 3: Gate Charge

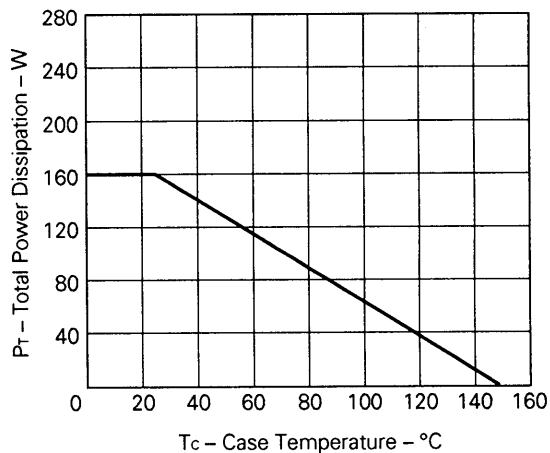


TYPICAL CHARACTERISTICS ($T_a = 25^\circ\text{C}$)

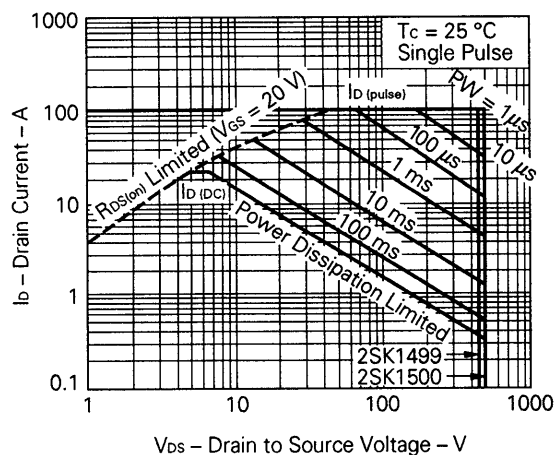
DERATING FACTOR OF FORWARD BIAS
SAFE OPERATING AREA



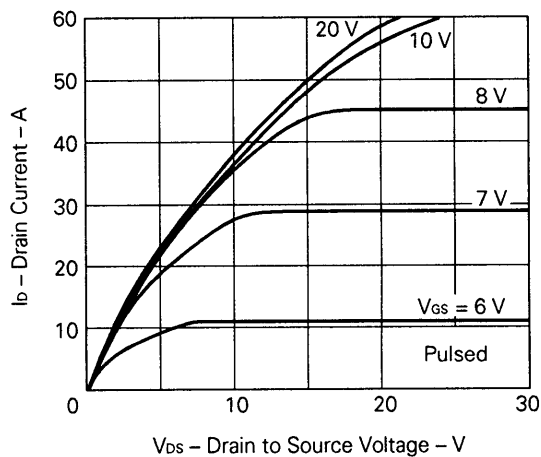
TOTAL POWER DISSIPATION vs.
CASE TEMPERATURE



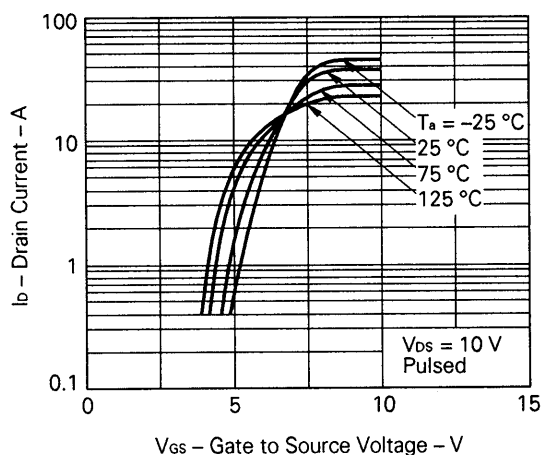
FORWARD BIAS SAFE OPERATING AREA

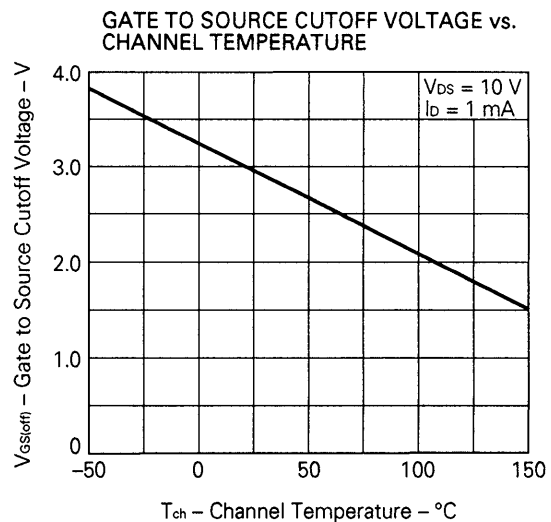
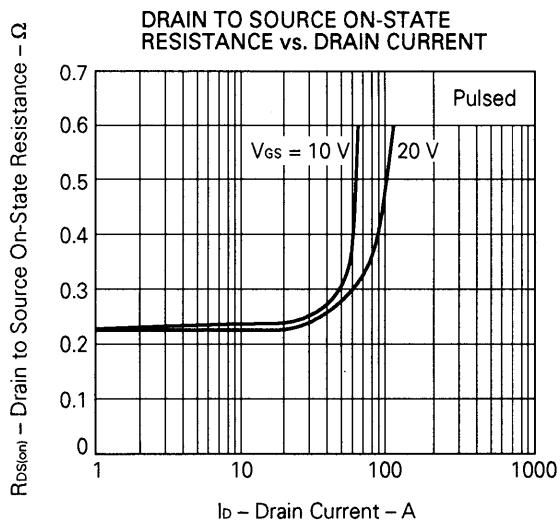
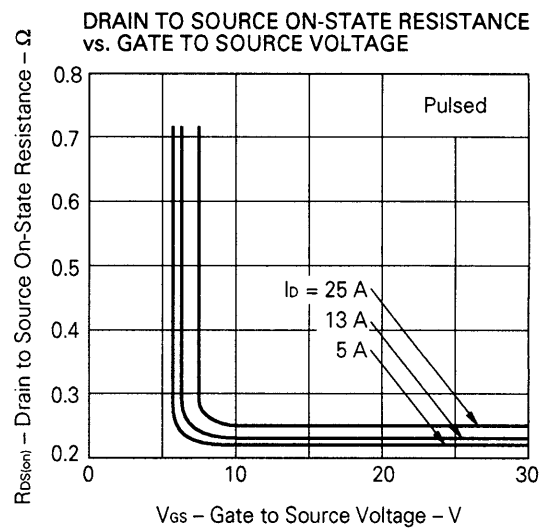
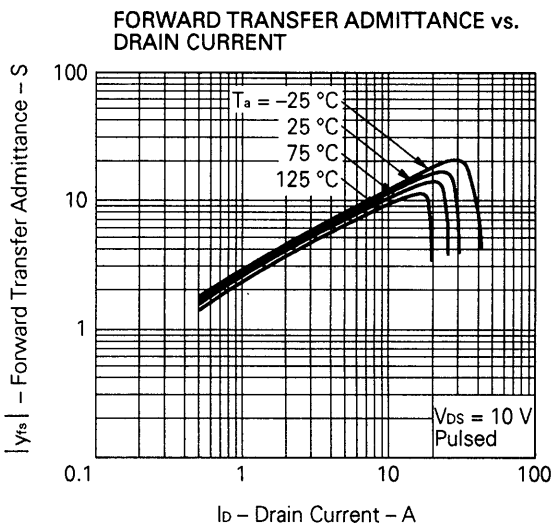
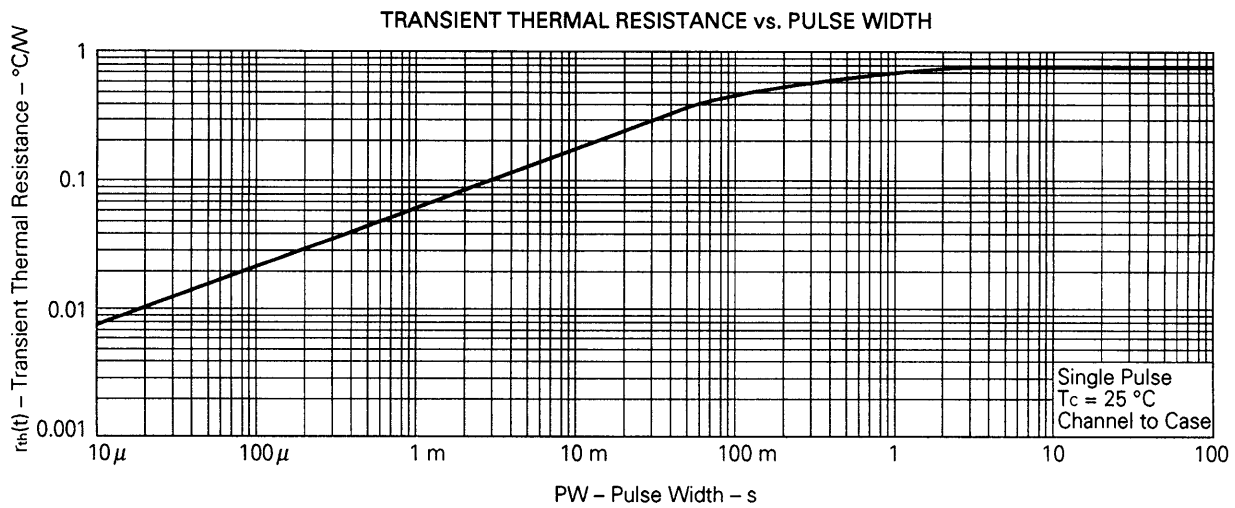


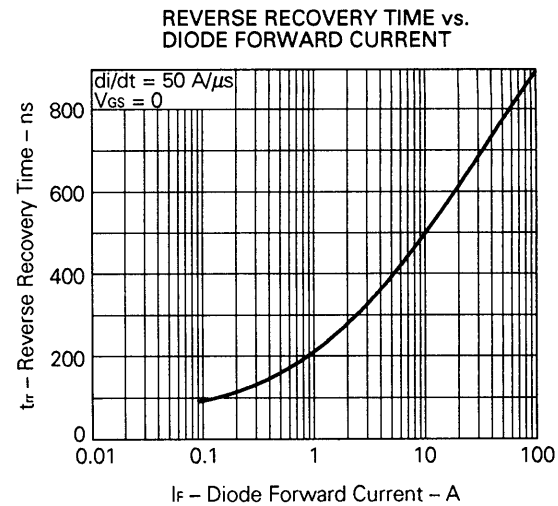
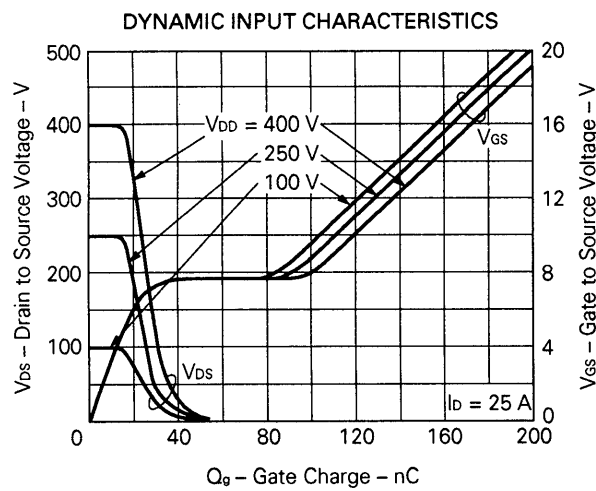
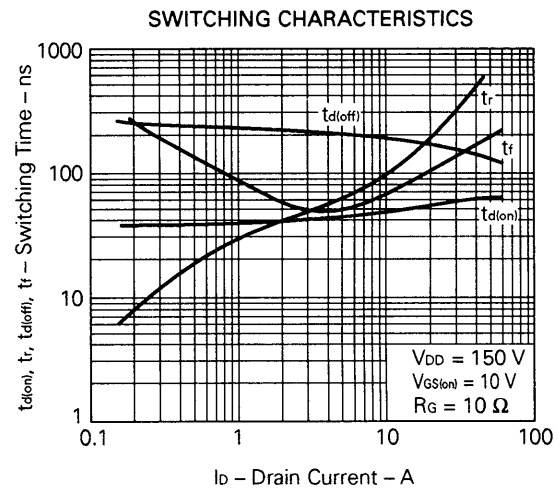
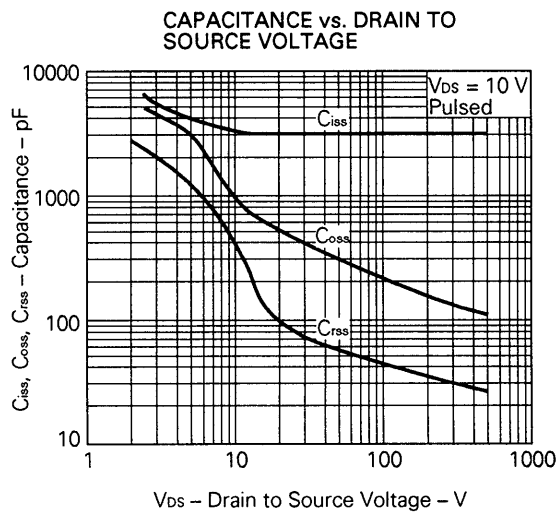
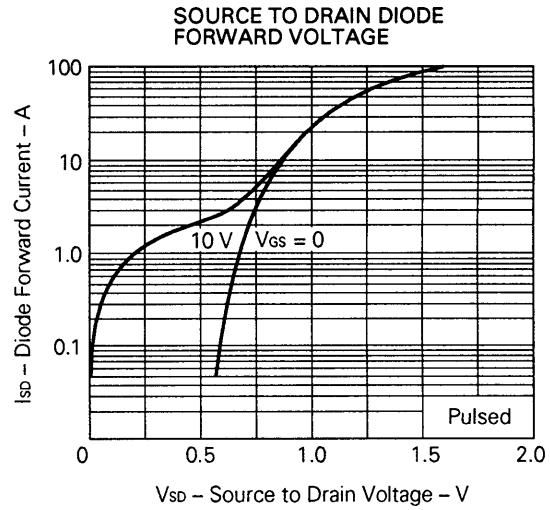
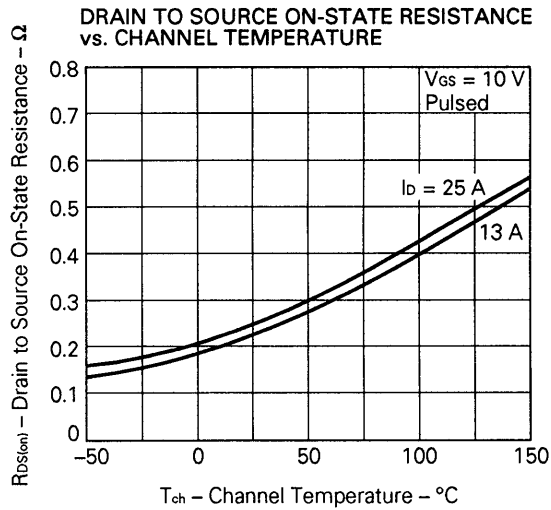
DRAIN CURRENT vs.
DRAIN TO SOURCE VOLTAGE



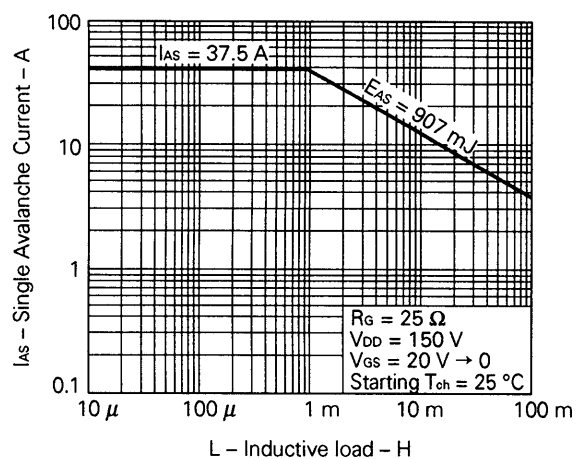
TRANSFER CHARACTERISTICS







SINGLE AVALANCHE CURRENT vs.
INDUCTIVE LOAD



SINGLE AVALANCHE ENERGY vs.
STARTING CHANNEL TEMPERATURE

